

## ABSTRACT

[0057] A method of forming self-aligned MRAM contacts is disclosed. MRAM stacks including an upper layer of a conductive material are formed over portions of integrated circuitry. An insulating material is formed over the substrate, including the MRAM stacks with the upper layer of conductive material. The insulating material is subsequently chemically mechanically polished or etched, stopping on the upper layer of conductive material, to expose portions of the conductive material which are used as self-aligned MRAM contacts.

The first of these is the fact that the
  $\text{H}^+$  ions are not free to move, but are
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